TOSHIBA TC7W32F/FU/FK

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7W32F, TC7W32FU, TC7W32FK

DUAL 2-INPUT OR GATE

The TC7W32 is a high speed C²MOS 2-INPUT OR GATE fabricated with silicon gate C²MOS technology.

It achives the high speed operation similar to equivalent LSTTL while maintaining the C²MOS low power dissipation.

The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES

• High Speed tpd = 6ns (Typ.) at

 $V_{CC} = 5V$

• Low Power Dissipation $I_{CC} = 1\mu A$ (Max.) at

 $Ta = 25^{\circ}C$

• High Noise Immunity $V_{NIH} = V_{NIL}$

= 28% V_{CC} (Min.)

Output Drive Capability 10 LSTTL Loads

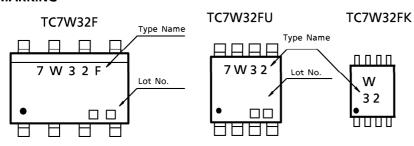
• Symmetrical Output Impedance ... $|I_{OH}| = I_{OL} = 4mA$

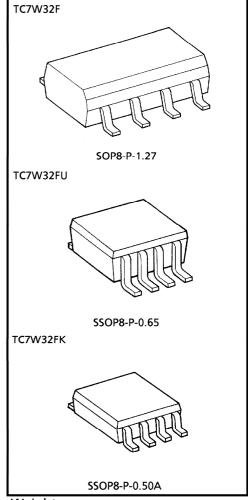
(Min.)

 $\bullet \quad \text{Balanced Propagation Delays} \ \dots \dots \quad t_{pLH} \dot{=} t_{pHL} \\$

Wide Operating Voltage Range ... V_{CC (opr)} = 2~6V

MARKING





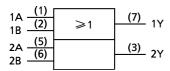
Weight

SOP8-P-1.27 : 0.05g (Typ.) SSOP8-P-0.65 : 0.02g (Typ.) SSOP8-P-0.50A : 0.01g (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	Vcc	- 0.5~7	V
DC Input Voltage	VIN	−0.5~V _{CC} +0.5	V
DC Output Voltage	VOUT	−0.5~V _{CC} +0.5	V
Input Diode Current	ΙΚ	± 20	mA
Output Diode Current	loк	± 20	mA
DC Output Current	IOUT	± 25	mA
DC V _{CC} /Ground Current	Icc	± 25	mA
Davier Dissipation	D-	300 (FM8, SM8)	\^/
Power Dissipation	PD	200 (US8)	mW
Storage Temperature	T _{stg}	-65∼150	°C
Lead Temperature (10s)	TL	260	°C

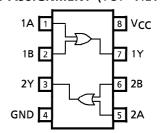
LOGIC DIAGRAM



TRUTH TABLE

А	В	Y
Н	Н	Н
L	Н	Н
Н	Ĺ	Н
L	L	L

PIN ASSIGNMENT (TOP VIEW)



RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	Vcc	2~6	V
Input Voltage	V _{IN}	0~V _{CC}	V
Output Voltage	Vout	0~V _{CC}	٧
Operating Temperature	T _{opr}	- 40∼85	°C
		$0 \sim 1000 \text{ (V}_{CC} = 2.0\text{V)}$	
Input Rise and Fall Time	t _r , t _f	$0 \sim 500 \ (V_{CC} = 4.5V)$	ns
		$0\sim 400 \ (V_{CC} = 6.0V)$	

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC SYMBOL		TEST CONDITION			Ta = 25°C			Ta = -40~85°C		UNIT
CHARACTERISTIC	3 TIVIBOL	TEST CONDITION		Vcc	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
High Lovel			2.0	1.5	_	_	1.5	_		
1 -	High-Level VIH	_		4.5	3.15	_	—	3.15	_	V
Input Voltage				6.0	4.2	_	_	4.2		
Lovelovel				2.0	_	_	0.5	_	0.5	
Low-Level	V _{IL}		_	4.5	—	_	1.35	_	1.35	V
Input Voltage				6.0	_	_	1.8	_	1.8	
		V _{IN} = V _{IH} or V _{IL}		2.0	1.9	2.0	_	1.9	_	
112.1.11			$I_{OH} = -20 \mu A$	4.5	4.4	4.5	—	4.4	_	
High-Level	VOH			6.0	5.9	6.0	—	5.9	_	l v l
Output Voltage			$I_{OH} = -4mA$	4.5	4.18	4.31		4.13	_	
			$I_{OH} = -5.2 \text{mA}$	6.0	5.68	5.80	—	5.63	_	
		V _{IN} = V _{IL}		2.0	_	0.0	0.1	_	0.1	
l			$I_{OL} = 20 \mu A$	4.5	—	0.0	0.1	_	0.1	
Low-Level	VOL			6.0	—	0.0	0.1	_	0.1	l v l
Output Voltage	"-		I _{OL} = 4mA	4.5	_	0.17	0.26	_	0.33	
			$I_{OL} = 5.2 mA$	6.0	—	0.18	0.26	_	0.33	
Input Leakage	lini	V.v V.a.a. 1	C or GND	6.0			± 0.1		± 1.0	
Current	IN	AIM = ACC		0.0	_	_	- 0.1	_	± 1.0	ا ا
Quiescent	laa	V V (or CND	6.0			1.0		10.0	μ A
Supply Current	lcc	AIM = ACC	$V_{IN} = V_{CC}$ or GND				1.0		10.0	

AC ELECTRICAL CHARACTERISTICS ($C_L = 15pF$, $V_{CC} = 5V$, Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	Т	UNIT		
CHARACTERISTIC	3 TIVIBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition	^t TLH			4	g	ns
Time	t _{THL}	_				113
Propagation Delay	t _{pLH}			6	12	ns
Time	t _{pHL}	_		0	12	113

AC ELECTRICAL CHARACTERISTICS ($C_L = 50pF$, Input $t_r = t_f = 6ns$)

CHARACTERISTIC SYMB		TEST CONDITION		Ta = 25°C			Ta = -4	UNIT	
CHARACTERISTIC STIVIBOL	STIVIBOL	TEST CONDITION		MIN.	TYP.	MAX.	MIN.	MAX.	CIVIT
Output Transition	t		2.0	_	25	75	_	95	
Time	t _{TLH}	_	4.5	—	7	15	_	19	ns
Time t _{THL}	THL		6.0	—	6	13	_	16	
$\begin{array}{ccc} \text{Propagation Delay} & t_{pLH} \\ \text{Time} & t_{pHL} \end{array}$	4		2.0	_	27	75	_	95	
	1 .'	_	4.5	—	8	15	_	19	ns
	l rbHΓ		6.0	—	7	13	_	16	
Input Capacitance	CIN	_		_	5	10	_	10	
Power Dissipation	C	(Note 1)			21				рF
Capacitance	C _{PD}	(Note 1)			21				

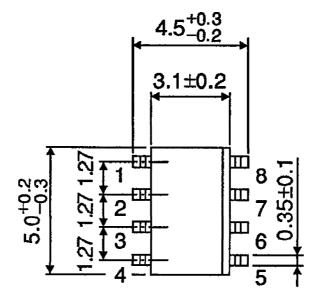
(Note 1): CPD is defined as the value of internal equivalent capacitance of IC which is calculated from the operating current consumption without load (refer to Test Circuit).

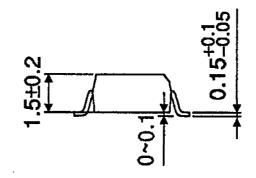
Average operating current can be obtained by the equation hereunder. $I_{CC}(opr) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 2$ (per gate)

PACKAGE DIMENSIONS

SOP8-P-1.27

Unit: mm

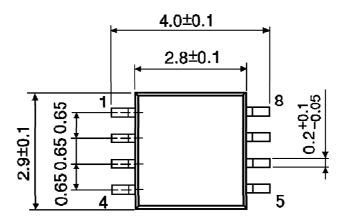


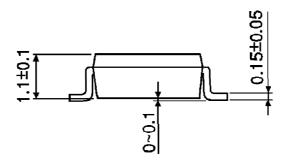


Weight: 0.05g (Typ.)

PACKAGE DIMENSIONS

SSOP8-P-0.65 Unit: mm

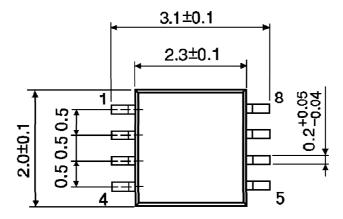


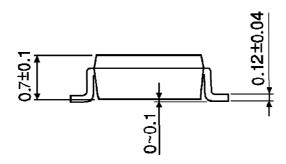


Weight: 0.02g (Typ.)

PACKAGE DIMENSIONS

SSOP8-P-0.50A Unit: mm





Weight: 0.01g (Typ.)

RESTRICTIONS ON PRODUCT USE

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